

P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (mA)
- 20	8 at V _{GS} = - 4.5 V	- 150
	12 at V _{GS} = - 2.5 V	- 125
	15 at V _{GS} = - 1.8 V	- 100
	20 at V _{GS} = - 1.5 V	- 30

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- High-Side Switching
- Low On-Resistance: 8 Ω
- Low Threshold: 0.9 V (typ.)
- Fast Switching Speed: 45 ns
- TrenchFET® Power MOSFETs: 1.5 V Rated
- ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC



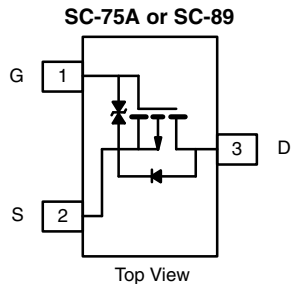
RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation



SC-75A (SOT-416): Si1031R
SC-89 (SOT-490): Si1031X

Marking Code: H

Ordering Information:

Si1031R-T1-GE3 (SC-75A, Lead (Pb)-free and Halogen-free)
Si1031X-T1-GE3 (SC-89, Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)							
Parameter	Symbol	Si1031R		Si1031X		Unit	
		5 s	Steady State	5 s	Steady State		
Drain-Source Voltage	V _{DS}	- 20				V	
Gate-Source Voltage	V _{GS}	± 6					
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	- 150	- 140	- 165	- 155	mA
		T _A = 85 °C	- 110	- 100	- 150	- 125	
Pulsed Drain Current ^a	I _{DM}	- 500		- 600		mW	
Continuous Source Current (Diode Conduction) ^a	I _S	- 250	- 200	- 340	- 240		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	280	250	340	300	mW
		T _A = 85 °C	145	130	170	150	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150				°C	
Gate-Source ESD Rating (HBM, Method 3015)	ESD	2000				V	

Notes:

a. Surface mounted on FR4 board.



SPECIFICATIONS (T _A = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.40		- 1.2	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 2.8 V		± 0.5	± 1.0	μA
		V _{DS} = 0 V, V _{GS} = ± 4.5 V		± 1.0	± 2.0	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 16 V, V _{GS} = 0 V		- 1	- 500	nA
		V _{DS} = - 16 V, V _{GS} = 0 V, T _J = 85 °C			- 10	μA
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 4.5 V	- 200			mA
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 150 mA			8	Ω
		V _{GS} = - 2.5 V, I _D = - 125 mA			12	
		V _{GS} = - 1.8 V, I _D = - 100 mA			15	
		V _{GS} = - 1.5 V, I _D = - 30 mA			20	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = 150 mA		0.4		S
Diode Forward Voltage ^a	V _{SD}	I _S = - 150 mA, V _{GS} = 0 V			- 1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 150 mA		1500		pC
Gate-Source Charge	Q _{gs}			150		
Gate-Drain Charge	Q _{gd}			450		
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 10 V, R _L = 65 Ω I _D ≅ - 150 mA, V _{GEN} = - 4.5 V, R _g = 10 Ω			55	ns
Rise Time	t _r				30	
Turn-Off Delay Time	t _{d(off)}				60	
Fall Time	t _f				30	

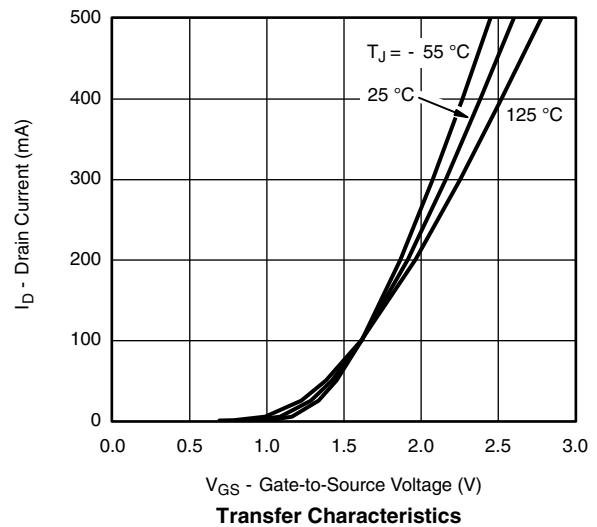
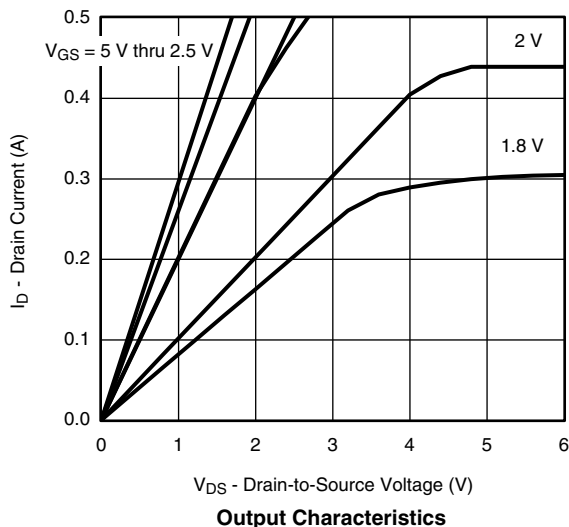
Notes:

a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.

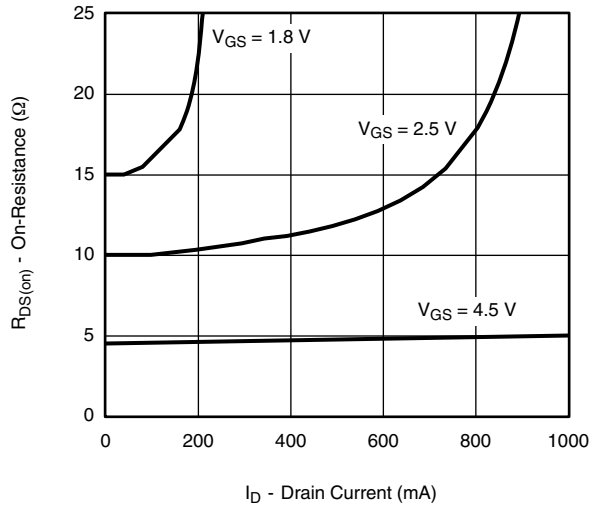
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

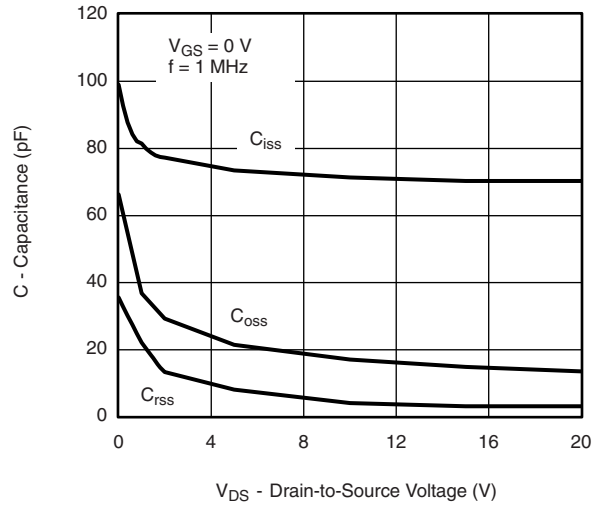
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



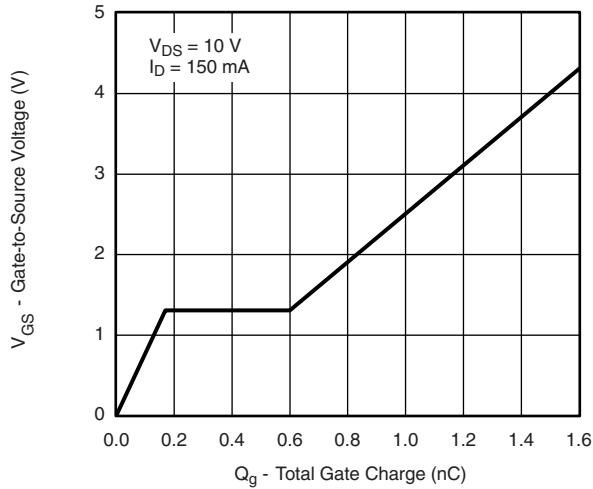
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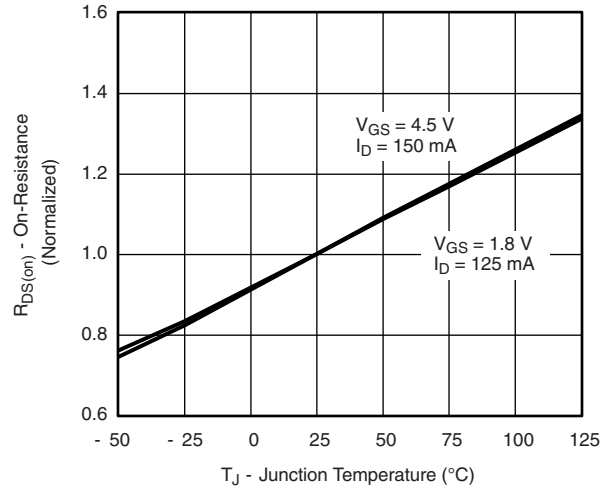
On-Resistance vs. Drain Current



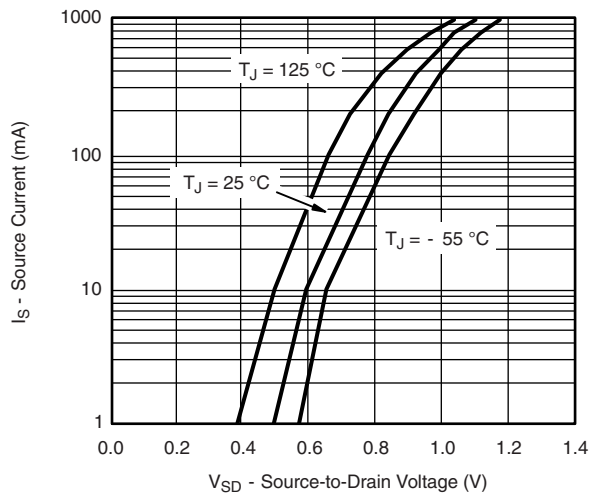
Capacitance



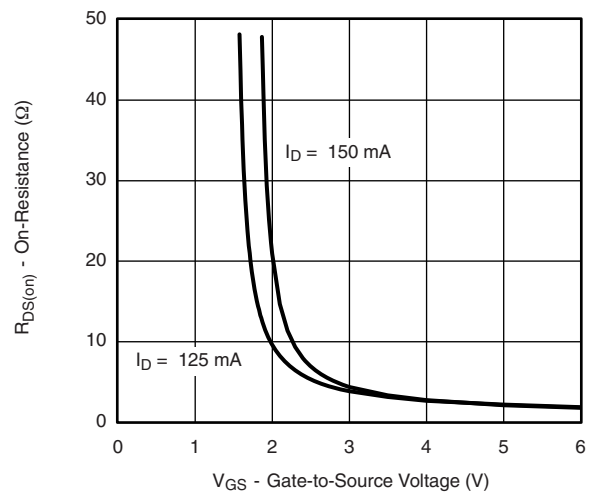
Gate Charge



On-Resistance vs. Junction Temperature

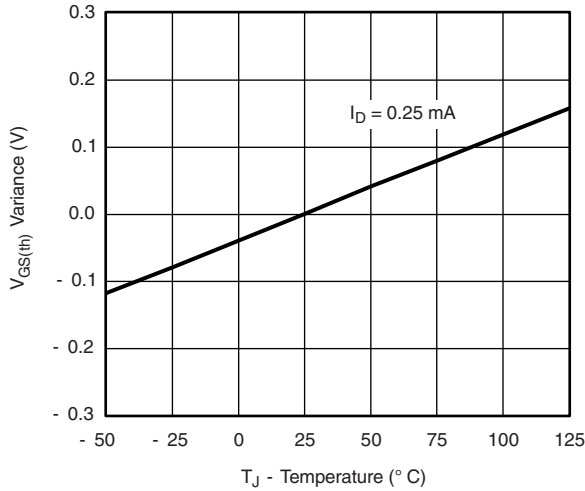


Surge-Drain Diode Forward Voltage

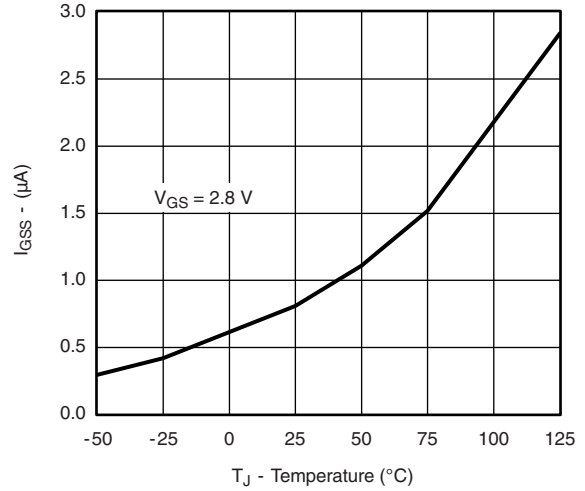


On-Resistance vs. Gate-to-Source Voltage

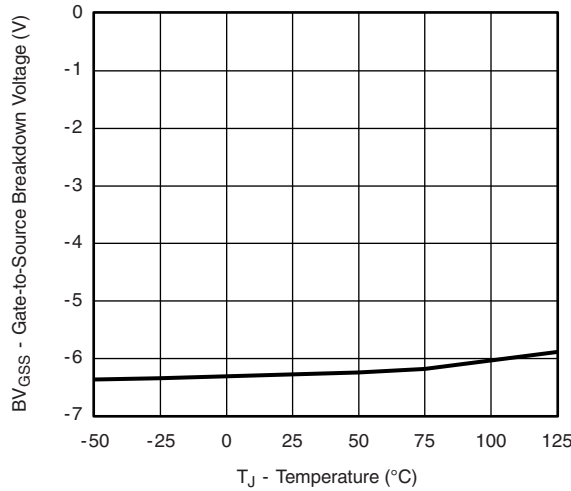
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



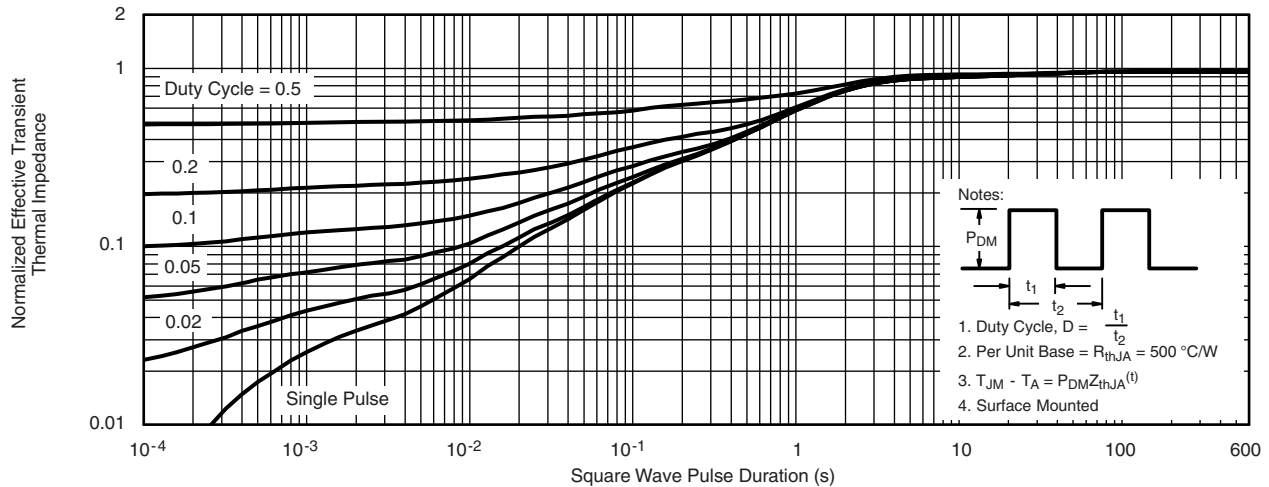
Threshold Voltage Variance vs. Temperature



I_{GSS} vs. Temperature



BV_{GSS} vs. Temperature

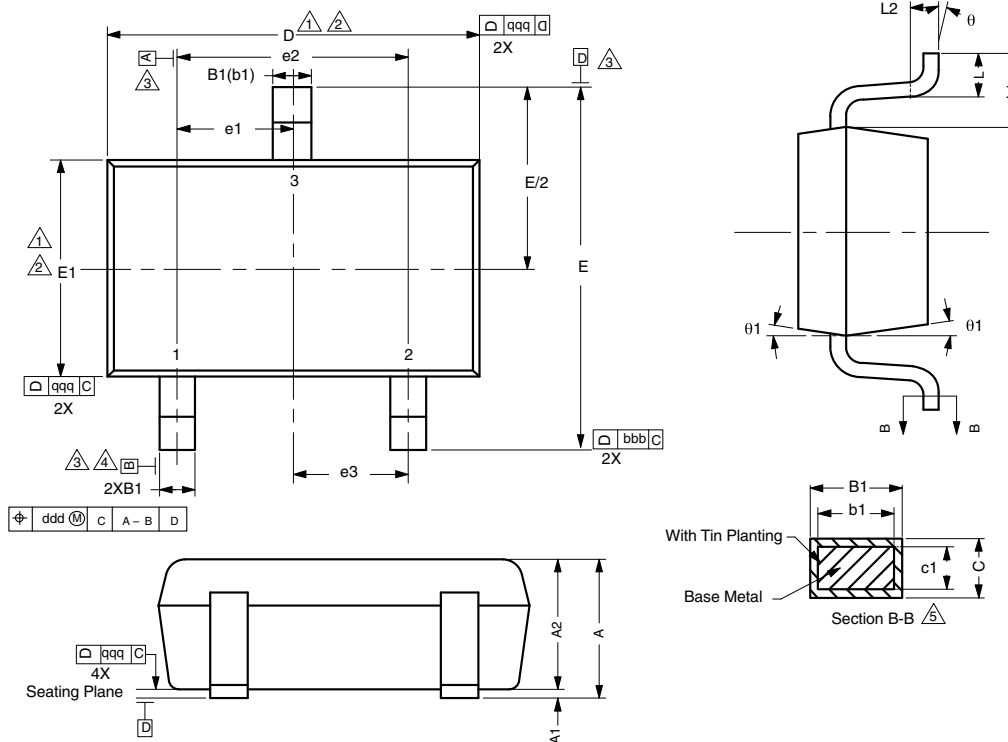


Normalized Thermal Transient Impedance, Junction-to-Ambient (SC-75A, Si1031R Only)

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SC-75A: 3-LEADS



Notes

Dimensions in millimeters will govern.

1. Dimension D does not include mold flash, protrusions or gate burrs. Mold flash protrusions or gate burrs shall not exceed 0.10 mm per end. Dimension E1 does not include Interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.10 mm per side.
2. Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.
3. Datums A, B and D to be determined 0.10 mm from the lead tip.
4. Terminal positions are shown for reference only.
5. These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIMENSIONS	TOLERANCES
aaa	0.10
bbb	0.10
ccc	0.10
ddd	0.10

DIM.	MILLIMETERS			NOTE
	MIN.	NOM.	MAX.	
A	-	-	0.80	
A ₁	0.00	-	0.10	
A ₂	0.65	0.70	0.80	
B ₁	0.19	-	0.24	5
b ₁	0.17	-	0.21	
c	0.13	-	0.15	5
c ₁	0.10	-	0.12	5
D	1.48	1.575	1.68	1, 2
E	1.50	1.60	1.70	
E ₁	0.66	0.76	0.86	1, 2
e ₁	0.50 BSC			
e ₂	1.00 BSC			
e ₃	0.50 BSC			
L	0.15	0.205	0.30	
L ₁	0.40 REF			
L ₂	0.15 BSC			
θ	0°	-	8°	
θ ₁	4°	-	10°	

ECN: E11-2210-Rev. D, 08-Aug-11
DWG: 5868

RECOMMENDED MINIMUM PADS FOR SC-75A: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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